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PTO/SB/08A (08-00)

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

### Complete if Known

Application Number	TBA
Filing Date	Herewith
First Named Inventor	Toru TANZAWA et al.
Group Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	001701.00240

### U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
Qu		5,570,315		Tanaka et al.	10/1996	
Qu		5,652,719		Tanaka et al.	07/1997	

### FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sub>3</sub>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

### OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
Qu		M. BAUER, et al., "A Multilevel-cell 32Mb Flash Memory" 1995 IEEE International Solid-State Circuits Conference, pp. 132-133	
Qu		M. OHKAWA, et al., "A 98mm <sup>2</sup> 3.3V 64Mb Flash Memory with FN-NOR Type 4-level Cell" 1996 IEEE International Solid-State Circuits Conference, pp. 36-37	
Qu		G. CAMPARDO, et al. "A 40mm <sup>2</sup> 3V 50MHz 64Mb 4-Level Cell NOR-Type Flash Memory", 2000 IEEE International Solid-State Circuits Conference, pg. 274	

Examiner Signature

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Date Considered

5/30/04

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